

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application)	<u>PATENT APPLICATION</u>
)	
Inventor:	Jian Chen, et al.)
)	Art Unit: 2824
Application No.:	10/765,963)
)	Examiner: Tran, Andrew Q.
Filed Date:	January 26, 2004)
)	Customer No.: 64948
Title: METHOD OF READING NAND MEMORY) TO COMPENSATE FOR COUPLING BETWEEN) STORAGE ELEMENTS		
)	
)	

RESPONSE A TO OFFICE ACTION UNDER 37 C.F.R. § 1.111

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

This RESPONSE A is in reply to the Office Action mailed September 27, 2006.

AMENDMENTS TO THE CLAIMS are reflected in the listing of claims which begin on page 2 of this Response.

AMENDMENTS TO THE ABSTRACT are reflected in the listing of claims which begin on page 7 of this Response.

AMENDMENTS TO THE DRAWINGS are reflected in the listing of claims which begin on page 8 of this Response.

REMARKS begin on Page 9 of this Response.